

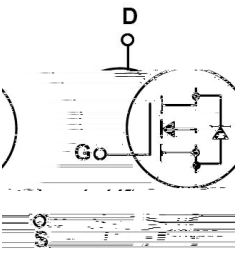
[illegible]



TO-252 N
N-CHANNEL MOSFET in a TO-252 Plastic Package.

$R_{DS(on)}$ C_{rss}
Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching, HF Product.

DC/DC
Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.



PIN1 G PIN 2 D PIN 3 S PIN 4 D

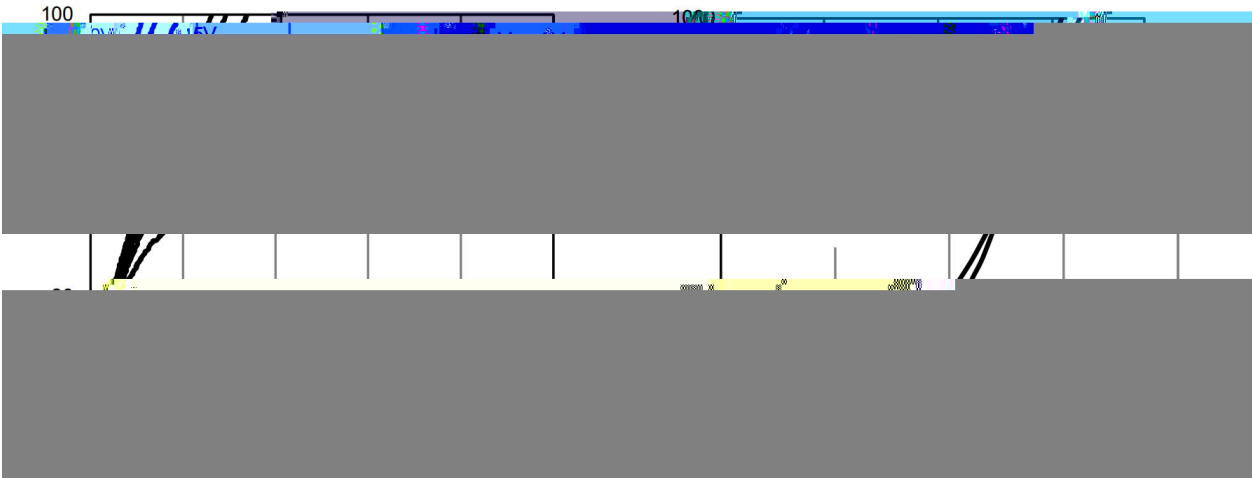
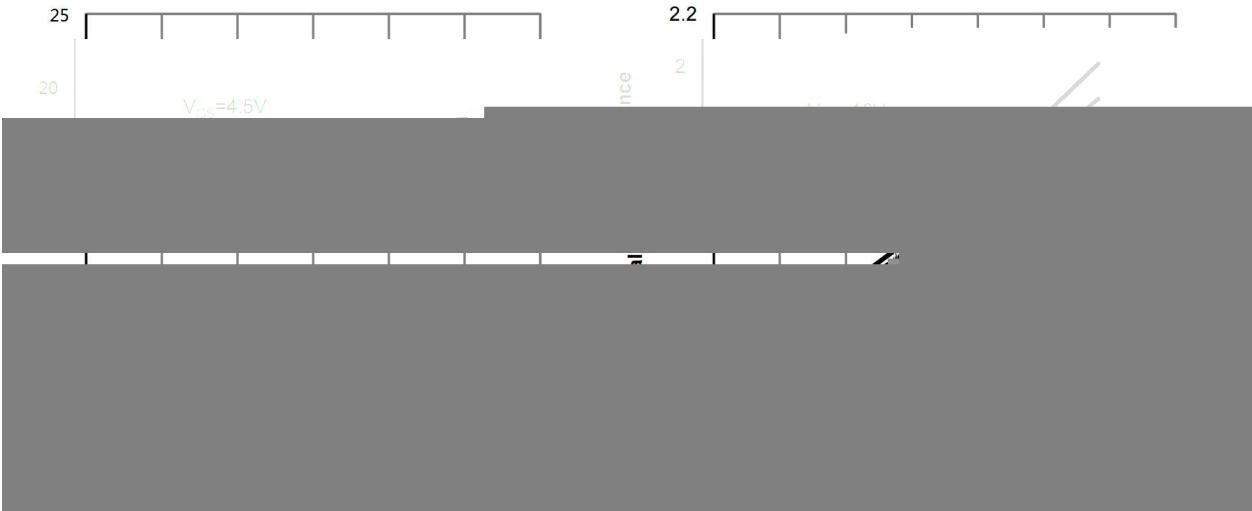
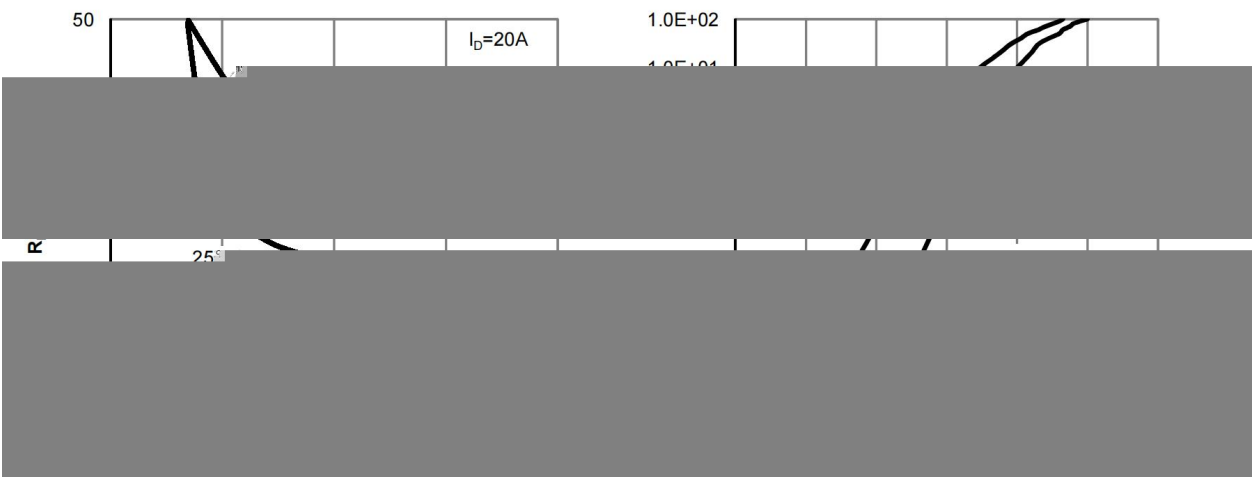
See Marking Instructions.



Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Drain Current		$I_D(T_c=25^{\circ}C)$	55	A
Drain Current - Pulsed		I_{DM}	138	A
Gate-Source Voltage		V_{GS}	± 20	V
Avalanche Current		I_{AS}	7.0	A
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	24.5	mJ
Power Dissipation		$P_D(T_c=25^{\circ}C)$	73	W
Storage Temperature Range		T_{stg}	-55 to 150	$^{\circ}C$
Thermal Resistance-Junction to Ambient	$t \leq 10s$	$R_{\theta JA}$	20	$^{\circ}C/W$
	Steady-State		50	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	1.7	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	100	108		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V$ $V_{GS}=0V$			1.0	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=20V$ $V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.5	1.8	2.5	V

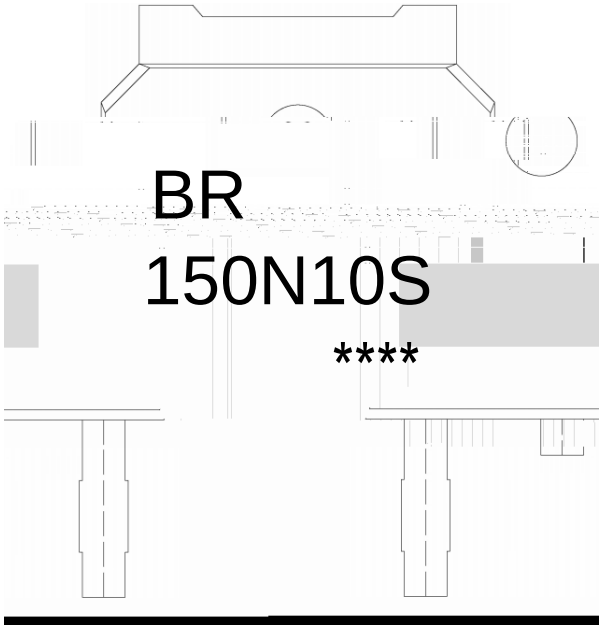
Static Drain-Source
On-





Rev.A Feb.-2022

http://



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BR□
150N10S□
****□

Note:
BR: Company Code
150N10S: Product Type Code
****: Lot No. Code, code change with Lot No

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Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- | | | | |
|---|-----------|-------------|---|
| 1 | 150 ~ 180 | 60 ~ 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | 2 ~ 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

260±5

10±1 sec.

Temp.:260±5℃

Time:10±1 sec

/ REEL

Package Type

Units

Dimension

(unit mm)